

# RJK0654DPB

60V, 30A, 8.3m $\Omega$  nax. Silicon N Channel Power MOS FET Power Switching

R07DS1052EJ0200 (Previous: REJ03G1880-0100)

Rev.2.00

Apr 09, 2013

### **Features**

- High speed switching
- Low drive current
- Low on-resistance  $R_{DS(on)} = 6.5 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V)}$
- Pb-free
- Halogen-free
- High density mounting

### **Outline**

RENESAS Package code: PTZZ0005DA-A (Package name: LFPAK)

5
D
1, 2, 3 Source 4 Gate 5 Drain

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                   | Symbol                      | Ratings     | Unit |
|--|-----------------------------|-------------|------|
| Drain to source voltage                | V <sub>DSS</sub>            | 60          | V    |
| Gate to source voltage                 | $V_{GSS}$                   | ±20         | V    |
| Drain current                          | I <sub>D</sub>              | 30          | А    |
| Drain peak current                     | I <sub>D(pulse)</sub> Note1 | 120         | А    |
| Body-drain diode reverse drain current | I <sub>DR</sub>             | 30          | А    |
| Avalanche current                      | I <sub>AP</sub> Note 2      | 30          | А    |
| Avalanche energy                       | E <sub>AS</sub> Note 2      | 6.8         | mJ   |
| Channel dissipation                    | Pch Note3                   | 55          | W    |
| Channel to Case Thermal Resistance     | θch-C                       | 2.27        | °C/W |
| Channel temperature                    | Tch                         | 150         | °C   |
| Storage temperature                    | Tstg                        | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at L=10uH, Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. Tc = 25°C

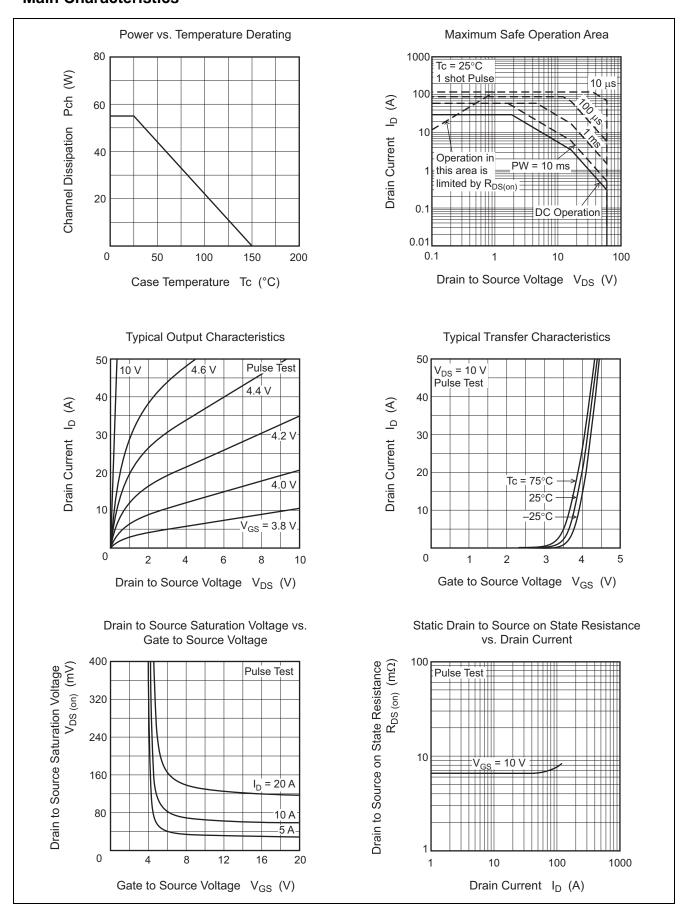
# **Electrical Characteristics**

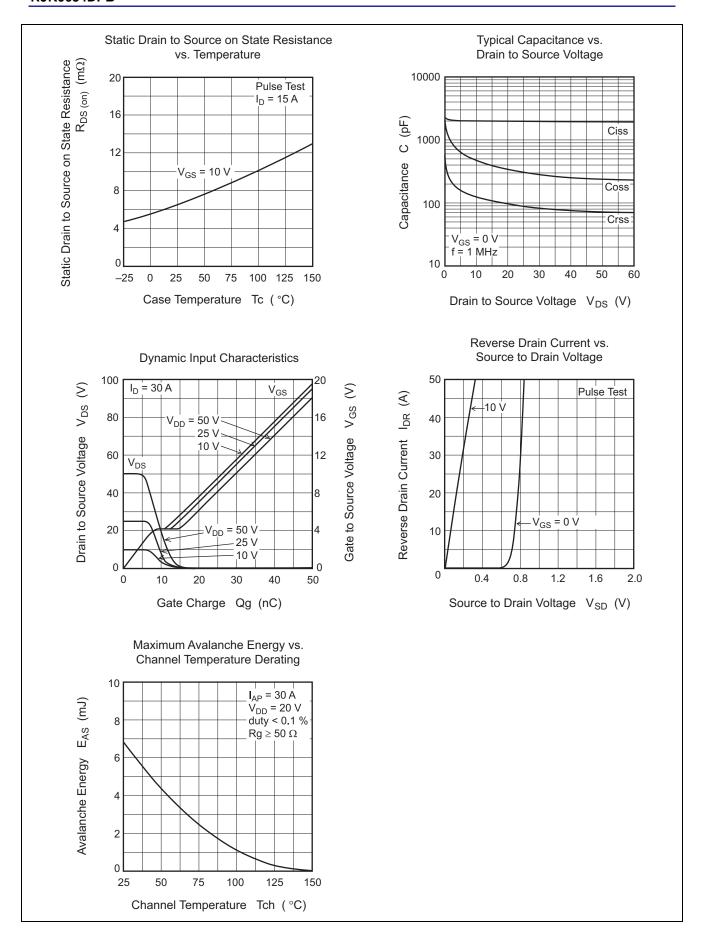
 $(Ta = 25^{\circ}C)$ 

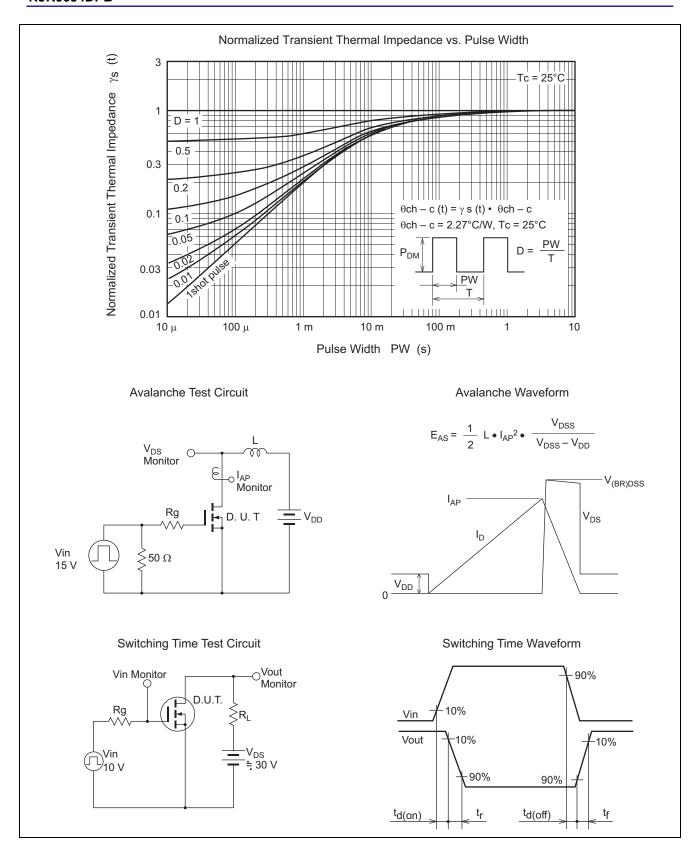
| Item                                       | Symbol               | Min | Тур  | Max  | Unit | Test Conditions  |
|--|----------------------|-----|------|------|------|--|
| Drain to source breakdown voltage          | V <sub>(BR)DSS</sub> | 60  | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$  |
| Gate to source leak current                | I <sub>GSS</sub>     | _   | _    | ±0.1 | μΑ   | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$  |
| Zero gate voltage drain current            | I <sub>DSS</sub>     | _   | _    | 1    | μΑ   | $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$  |
| Gate to source cutoff voltage              | V <sub>GS(off)</sub> | 2.0 | _    | 4.0  | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$  |
| Static drain to source on state resistance | R <sub>DS(on)</sub>  | _   | 6.5  | 8.3  | mΩ   | $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$                                       |
| Forward transfer admittance                | y <sub>fs</sub>      | _   | 39   | _    | S    | $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$                                       |
| Input capacitance                          | Ciss                 | _   | 2000 | _    | pF   | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$   |
| Output capacitance                         | Coss                 | _   | 475  | _    | pF   | f = 1 MHz  |
| Reverse transfer capacitance               | Crss                 | _   | 125  | _    | pF   |  |
| Gate Resistance                            | Rg                   | _   | 0.5  | _    | Ω    |  |
| Total gate charge                          | Qg                   | _   | 27   | _    | nC   | $V_{DD} = 25 \text{ V}, V_{GS} = 10 \text{ V},$  |
| Gate to source charge                      | Qgs                  | _   | 9.0  | _    | nC   | I <sub>D</sub> = 30 A  |
| Gate to drain charge                       | Qgd                  | _   | 4.5  | _    | nC   |  |
| Turn-on delay time                         | t <sub>d(on)</sub>   | _   | 12   | _    | ns   | $V_{GS} = 10 \text{ V}, I_D = 15 \text{ A},$   |
| Rise time                                  | t <sub>r</sub>       | _   | 6.8  | _    | ns   | $\begin{aligned} V_{DD} &\cong 30 \text{ V, } R_L = 2 \Omega, \\ Rg &= 4.7 \Omega \end{aligned}$ |
| Turn-off delay time                        | t <sub>d(off)</sub>  | _   | 32   | _    | ns   |  |
| Fall time                                  | t <sub>f</sub>       | _   | 9.2  | _    | ns   |  |
| Body-drain diode forward voltage           | $V_{DF}$             | _   | 0.8  | 1.1  | V    | $I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}^{\text{Note4}}$  |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>      | _   | 40   | _    | ns   | I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V   |
|  |                      |     |      |      |      | $di_F/dt = 100 \text{ A}/ \mu\text{s}$   |

Notes: 4. Pulse test

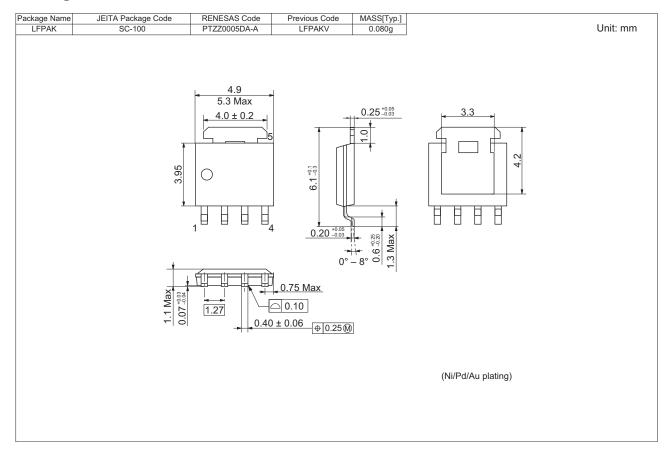
## **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK0654DPB-00-J5 | 2500 pcs | Taping             |

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Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Milliboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 i. nunLu Haidian District. Beiiing 100083. P.R.China

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852 2869-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949 Tel: +65-6213-0200, Fax: +65-6213-0300

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Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

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